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(54) Title: PLANARIZATION OF METAL CONTAINER STRUCTURES

(57) Abstract: A conductive material is provided in an opening formed in an insulative material. The process involves first forming a conductive material over at least a portion of the opening and over at least a portion of the insulative material which is outside of the opening. Next, a metal-containing fill material is formed over at least a portion of the conductive material which is inside the opening and which is also over the insulative material outside of the opening. The metal-containing at least partially fills the opening. At least a portion of both the metal-containing material and the conductive material outside of the openinng is then removed. Thereafter, at least a portion of the metal-containing fill material which is inside the opening is then removed.